

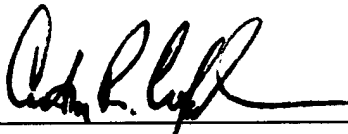
MARTIN, T. et al.
Serial No. unknown

REMARKS

Attached hereto is a marked-up version of the changes made to the specification and claims by the current amendment. The attached page(s) is captioned "**Version With Markings To Show Changes Made.**"

Respectfully submitted,

NIXON & VANDERHYE P.C.

By: 
Arthur R. Crawford
Reg. No. 25,327

ARC:ecb
1100 North Glebe Road, 8th Floor
Arlington, VA 22201-4714
Telephone: (703) 816-4000
Facsimile: (703) 816-4100

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE SPECIFICATION

Page 1, before the first line, insert as a separate paragraph:

This application is the U.S. national phase of international application PCT/GB00/02145 filed 02/06/2000, which designated the U.S..

IN THE CLAIMS

3. A method according to Claim 1 ~~or 2~~ characterised in that the mechanical shadow mask comprises a silicon wafer (92) having etched apertures (23) and an oxide film coating (91) upon which deposition does not occur at temperatures used for growth by chemical beam epitaxy.

4. A method according to ~~any preceding claim~~ claim 1 characterised in that the semiconductor device is a device (31, 100) for guiding radiation.